BLF8G24LS-150V; BLF8G24LS-150GV Power LDMOS transistor

AMPLEON

Rev. 4 — 1 September 2015

Product data sheet

Product profile

1.1 General description

150 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25$ °C in a common source class-AB production test circuit.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	Gp	η_D	ACPR _{5M}
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2300 to 2400	1300	28	45	19	33	-30 <u>[1]</u>

^{[1] 3}GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz. Channel bandwidth is 3.84 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (70 MHz typical)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range

2. Pinning information

Table 2. Pinning

Tubic .	able 2. Finning					
Pin	Description	Simplified outline	Graphic symbol			
BLF8	G24LS-150V (SOT1244B)					
1	drain	4 1 5	4			
2	gate	4 1 5 	6,7→1 4,5			
3	source [1]		2			
4	decoupling lead	3	3			
5	decoupling lead		aaa-003619			
6	n.c.					
7	n.c.	6 2 7				
BLF8	G24LS-150GV (SOT1244C)					
1	drain		_			
2	gate	4 1 5 	6 7 → 1 → 4,5			
3	source [1]		6,7			
4	decoupling lead		3			
5	decoupling lead	6 2 7	aaa-003619			
6	n.c.	6 2 7				
7	n.c.					

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package		
	Name	lame Description		
BLF8G24LS-150V	-	earless flanged ceramic package; 6 leads	SOT1244B	
BLF8G24LS-150GV	-	earless flanged ceramic package; 6 leads	SOT1244C	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 45 W	0.30	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 216 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 1300 mA	1.6	2	2.4	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	4.5	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	40	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	450	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 10.8 A	-	16	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 7.56 A$	-	0.06	-	Ω

Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF, carrier spacing 5 MHz; f_1 = 2302.5 MHz; f_2 = 2307.5 MHz; f_3 = 2392.5 MHz; f_4 = 2397.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1300 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 45 W	17.5	19	-	dB
RLin	input return loss	P _{L(AV)} = 45 W	-	-10	-7	dB
η_{D}	drain efficiency	P _{L(AV)} = 45 W	29	33	-	%
ACPR _{5M}	adjacent channel power ratio (5 MHz)	P _{L(AV)} = 45 W	-	-30	-27	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF8G24LS-150V and BLF8G24LS-150GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 1300 \text{ mA}$; $P_L = 150 \text{ W}$ (CW); f = 2300 MHz.

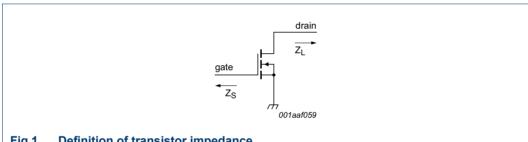
7.2 Impedance information

Table 8. **Typical impedance**

Measured load-pull data; $I_{Dq} = 1300 \text{ mA}$; $V_{DS} = 28 \text{ V}$.

f	Z _S [1]	Z _L [1]
(MHz)	(Ω)	(Ω)
BLF8G24LS-150V		
2300	1.25 – j4.11	2.95 – j1.20
2400	2.34 – j5.50	2.88 – j1.31
2500	5.65 – j6.35	2.80 – j1.35
BLF8G24LS-150GV		
2300	1.29 – j5.78	3.13 – j3.26
2400	2.15 – j7.09	2.78 – j3.44
2500	6.61 – j7.57	2.98 – j3.66

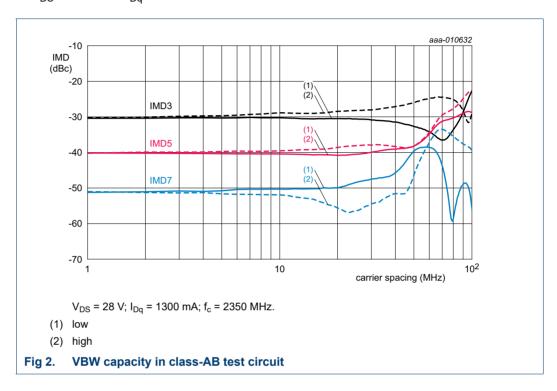
[1] Z_S and Z_L defined in Figure 1.



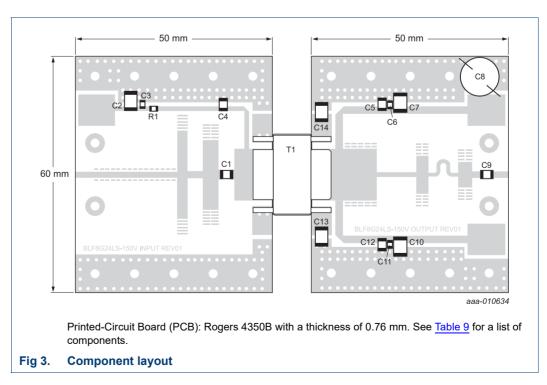
Definition of transistor impedance Fig 1.

7.3 VBW in a class-AB operation

The BLF8G24LS-150V shows 70 MHz (typical) video bandwidth (IMD third-order intermodulation inflection point) in a class-AB test circuit in the 2.3 GHz to 2.4 GHz band at V_{DS} = 28 V and I_{Dg} = 1.3 A.



7.4 Test circuit



BLF8G24LS-150V_8G24LS-150GV#4

Table 9. List of components

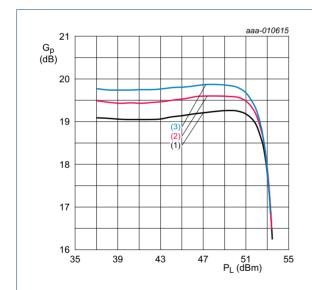
See Figure 3 for component layout.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	1.2 pF [1]	ATC 800B
C2	multilayer ceramic chip capacitor	1 μF	Murata
C3	multilayer ceramic chip capacitor	100 nF [2]	Murata
C4, C5, C9, C12	multilayer ceramic chip capacitor	24 pF [1]	ATC 800B
C6, C11	multilayer ceramic chip capacitor	220 nF [2]	Murata
C7, C10, C13, C14	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata
C8	electrolytic capacitor	> 470 μF, 63 V	
R1	chip resistor	4.7 Ω, 1 % tolerance	SMD 0805
T1	transistor	-	Ampleon BLF8G24LS-150V

- [1] American Technical Ceramics type 800B or capacitor of same quality.
- [2] Murata or capacitor of same quality.

7.5 Graphical data

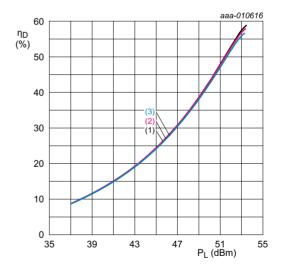
7.5.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 1300 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 4. Power gain as a function of output power; typical values

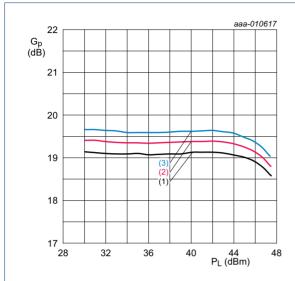


 V_{DS} = 28 V; I_{Dq} = 1300 mA; t_p = 100 μ s; δ = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 5. Drain efficiency as a function of out power; typical values

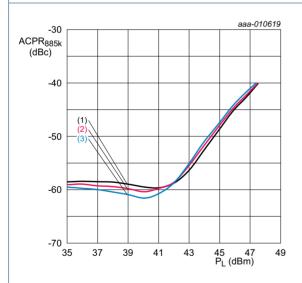
7.5.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

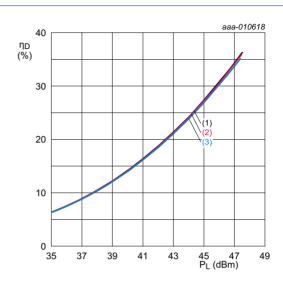
Fig 6. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

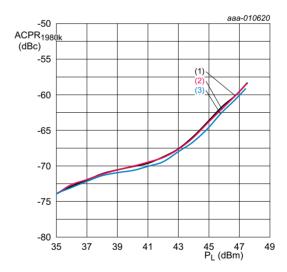
Fig 8. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 7. Drain efficiency as a function of output power; typical values



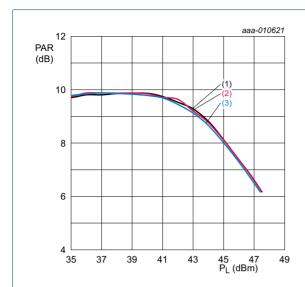
 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 9. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

BLF8G24LS-150(G)V

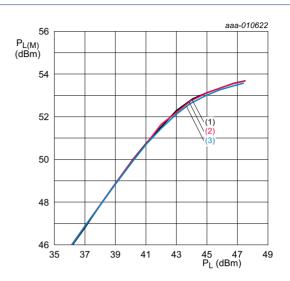
Power LDMOS transistor



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 10. Peak-to-average ratio as a function of output power; typical values

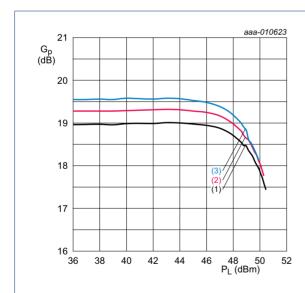


 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 11. Peak output power as a function of output power; typical values

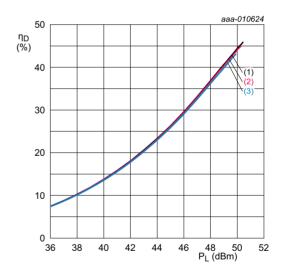
7.5.3 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 12. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

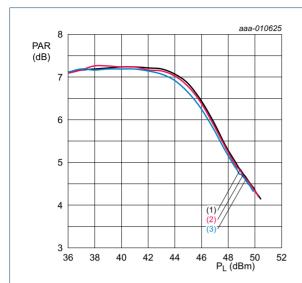
- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 13. Drain efficiency as a function of output power; typical values

8 of 16

BLF8G24LS-150(G)V

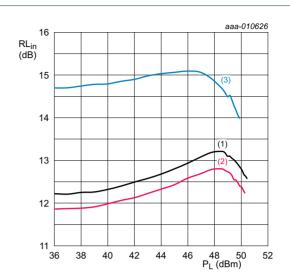
Power LDMOS transistor



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 14. Peak-to-average ratio as a function of output power; typical values

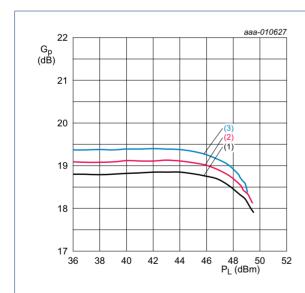


 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 15. Input return loss as a function of output power; typical values

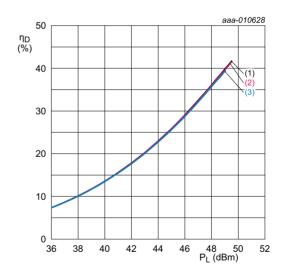
7.5.4 2-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

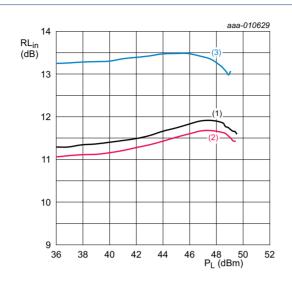
Fig 16. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

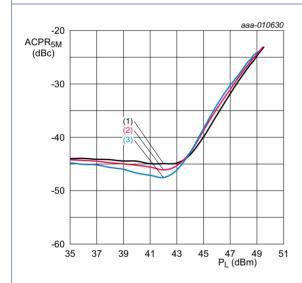
Fig 17. Drain efficiency as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

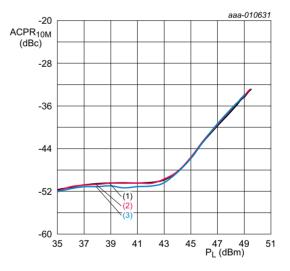
Fig 18. Input return loss as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 19. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 20. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

Package outline

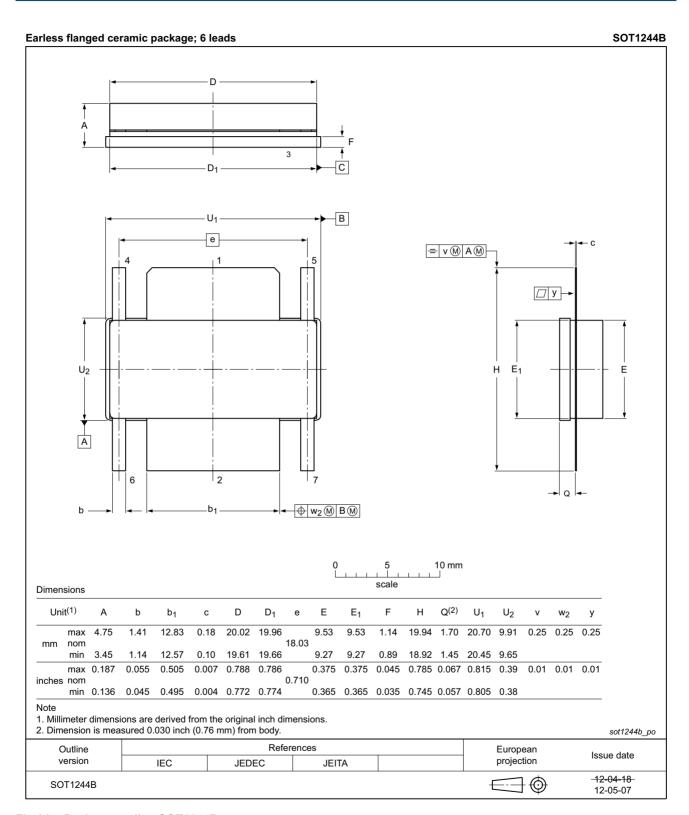


Fig 21. Package outline SOT1244B

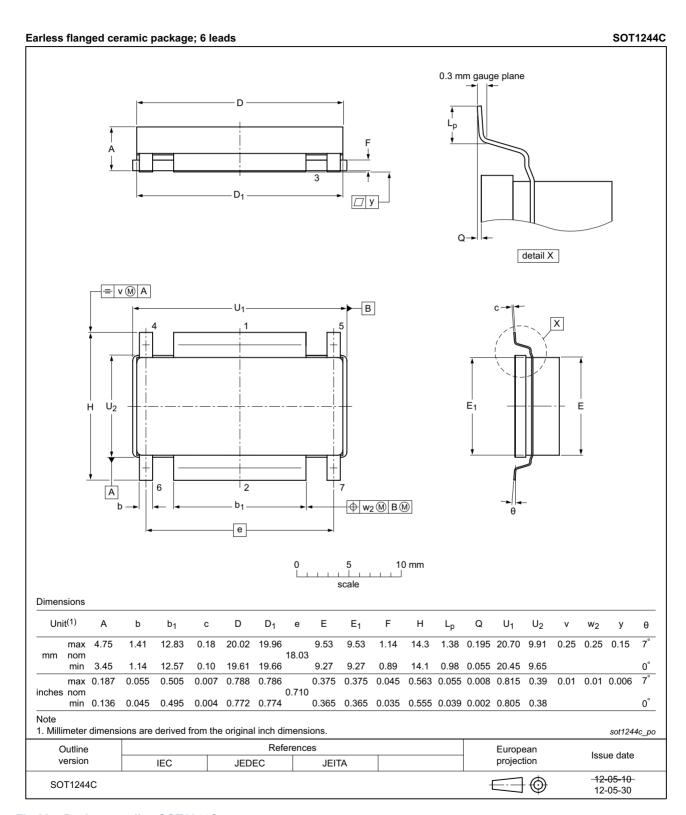


Fig 22. Package outline SOT1244C

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
3GPP	ord Generation Partnership Project	
CCDF	Complementary Cumulative Distribution Function	
CW	Continuous Wave	
DPCH	Dedicated Physical CHannel	
ESD	ElectroStatic Discharge	
IS-95	Interim Standard 95	
LDMOS	Laterally Diffused Metal Oxide Semiconductor	
MTF	Median Time to Failure	
PAR	Peak-to-Average Ratio	
SMD	Surface Mounted Device	
VBW	Video BandWidth	
VSWR	Voltage Standing Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF8G24LS-150V_8G24LS-150GV#4	20150901	Product data sheet		BLF8G24LS-150V_ 8G24LS-150GV v.3	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLF8G24LS-150V_8G24LS-150GV v.3	20140512	Product data sheet	-	BLF8G24LS-150V_ 8G24LS-150GV v.2	
BLF8G24LS-150V_8G24LS-150GV v.2	20140224	Objective data sheet	-	BLF8G24LS-150V_ 8G24LS-150GV v.1	
BLF8G24LS-150V_8G24LS-150GV v.1	20131104	Objective data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.	
Product [short] data sheet	Production	This document contains the product specification.	

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL https://www.ampleon.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Ampleon does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Ampleon sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Ampleon and its customer, unless Ampleon and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Ampleon product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Ampleon does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Ampleon takes no responsibility for the content in this document if provided by an information source outside of Ampleon.

In no event shall Ampleon be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Ampleon' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Ampleon.

Right to make changes — Ampleon reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Ampleon products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an

Ampleon product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Ampleon and its suppliers accept no liability for inclusion and/or use of Ampleon products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Ampleon makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Ampleon products, and Ampleon accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Ampleon product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Ampleon does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Ampleon products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Ampleon does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Ampleon products are sold subject to the general terms and conditions of commercial sale, as published at http://www.ampleon.com/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Ampleon hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Ampleon products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

BLF8G24LS-150V 8G24LS-150GV#4

All information provided in this document is subject to legal disclaimers.

© Ampleon The Netherlands B.V. 2015. All rights reserved.

BLF8G24LS-150(G)V

Power LDMOS transistor

Non-automotive qualified products — Unless this data sheet expressly states that this specific Ampleon product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Ampleon accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Ampleon' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Ampleon' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Ampleon for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Ampleon' standard warranty and Ampleon' product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own Any reference or use of any 'NXP' trademark in this document or in or on the surface of Ampleon products does not result in any claim, liability or entitlement vis-à-vis the owner of this trademark. Ampleon is no longer part of the NXP group of companies and any reference to or use of the 'NXP' trademarks will be replaced by reference to or use of Ampleon's own trademarks

13. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

AMPLEON

BLF8G24LS-150(G)V

Power LDMOS transistor

14. Contents

1	Product profile	. 1
1.1	General description	. 1
1.2	Features and benefits	
1.3	Applications	. 1
2	Pinning information	. 2
3	Ordering information	. 2
4	Limiting values	. 2
5	Thermal characteristics	. 3
6	Characteristics	. 3
7	Test information	. 3
7.1	Ruggedness in class-AB operation	. 3
7.2	Impedance information	
7.3	VBW in a class-AB operation	
7.4	Test circuit	. 5
7.5	Graphical data	. 6
7.5.1	Pulsed CW	. 6
7.5.2	IS-95	
7.5.3	1-Carrier W-CDMA	
7.5.4	2-Carrier W-CDMA	. 9
8	Package outline	11
9	Handling information	13
10	Abbreviations	13
11	Revision history	13
12	Legal information	14
12.1	Data sheet status	14
12.2	Definitions	14
12.3	Disclaimers	14
12.4	Trademarks	15
13	Contact information	15
4.4	0	40

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

NXP:

BLF8G24LS-150GVJ BLF8G24LS-150VU BLF8G24LS-150VJ BLF8G24LS-150GVQ